

Proximity Switches

Order code	Manufacturer code	Description
61-1410	UZC250	RETRO-REFLECT.NPN PHOTO SENSOR (C250)
61-1415	UZC2505	RETRO-REFLECT.PNP PHOTO SENSOR

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The enclosed information is believed to be correct, Information may change 'without notice' due to	Revision A
product improvement. Users should ensure that the product is suitable for their use. E. & O. E.	04/07/2003

Cylindrical Photoelectric Sensors

Matsushita - Retroreflective Type UZC250 (NPN) & UZC2505 (PNP)

The UZC250 & UZC2505 Sensors, each package consists of a combined Projector and Receiving Sensor

SPECIFICATIONS

DC type sensors

Reference No.		UZC250	UZC2505	
Sensing mode		Retroreflective (*1)	Retroreflective	
Trans	istor output type	NPN	PNP	
Sensi	ng range	3m (*2)		
Sensi	ng object	Opaque & translucent objects of min. Ø50mm (*2)		
Hysteresis		-		
	atability	0.1mm or less		
(vertical direction for a light axis)		0. Thin of less		
Supply voltage		10 to 30V DC Ripple P-P : ±10% or less		
Consumption		25mA		
Output		<npn output="" type=""> NPN open-collector transistor Current sink: Max. 100mA Applied voltage: 30V DC or less Residual voltage: 1.5V DC or less (at 100mA current sink)</npn>	<pnp output="" type=""> PNP open-collector transistor Current source: Max. 100mA Applied voltage: 30V DC or less Residual voltage: 1.5V DC or less (at 100mA current source)</pnp>	
Output operation		Selection of light-ON/Dark-ON by a control input wire		
Short-circuit protection		Equipped		
Response time		2ms or less		
Emission disable function		-		
Operation indicator		Red LED (turns on when the output is in the ON state) Thru-beam sensor is provided to the receiver		
Emiss	ion indicator	-		
	Protection	IP67 (IEC)		
JCe	Ambient temperature	-25 to +55°C (with no dew nor ice condensation), Storage: -30 to +70°C		
itar	Ambient humidity	35 to 85% RH, Storage: 35 to 85% RH		
sis	Ambient light	Sun light: 11,000 I x at the light-receiving face, Incandescent light: 3,500 I x at the light-receiving face		
Le	Noise	Power line: 240Vp with 0.5µs pulse duration		
nta	10.50	Radiation: 300Vp with 0.5µs pulse duration (by a noise simulator)		
nei	Dielectric	1,000 AC applied between the live parts and enclosure for 1 min.		
ror	Insulation	Min. 20M Ω applied between the live parts and enclosure at 250V DC		
Enviromental resistance	Vibration	1.5mm {Max. 10G} amplitude at the frequency of 10 to 500Hz in each of X, Y and Z directions for 2 hours each in the power OFF state		
Shock		500m/s ² {approx. 50G} impulse in each of X, Y and Z directions for 3 times each in the power OFF state		
Emitting element		Infrared LED (modulated)		
Material		Enclosure: PBT (grey), Lens: Polycarbonate		
Cable		0.34mm ² x 4 cores with 2m of cabtyre cable (3 cores for the emitter only)		
Cable extension		Extensible up to 100m by using. 0.34mm ² or more cable (Thru-beam sensor: each of an emitter and a receiver)		
Weight		Approx. 100g		
Accessories		Nut: 2 pcs.		

(*1) A reflector is not supplied with the retroreflective sensor
(*2) The sensing range and sensing object of the retroreflective sensor is the figure a UZZ112 reflector



SENSING FIELDS



